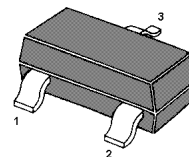


MMBTSB624 PNP Silicon Epitaxial Planar Transistor

For use in small type equipments, especially recommended or hybrid circuit and other applications

The transistor is subdivided into five groups A, B, C, D and E, according to its DC current gain.



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	30	V
Collector Emitter Voltage	$-V_{CEO}$	25	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	700	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25\text{ }^\circ\text{C}$ unless otherwise specified)

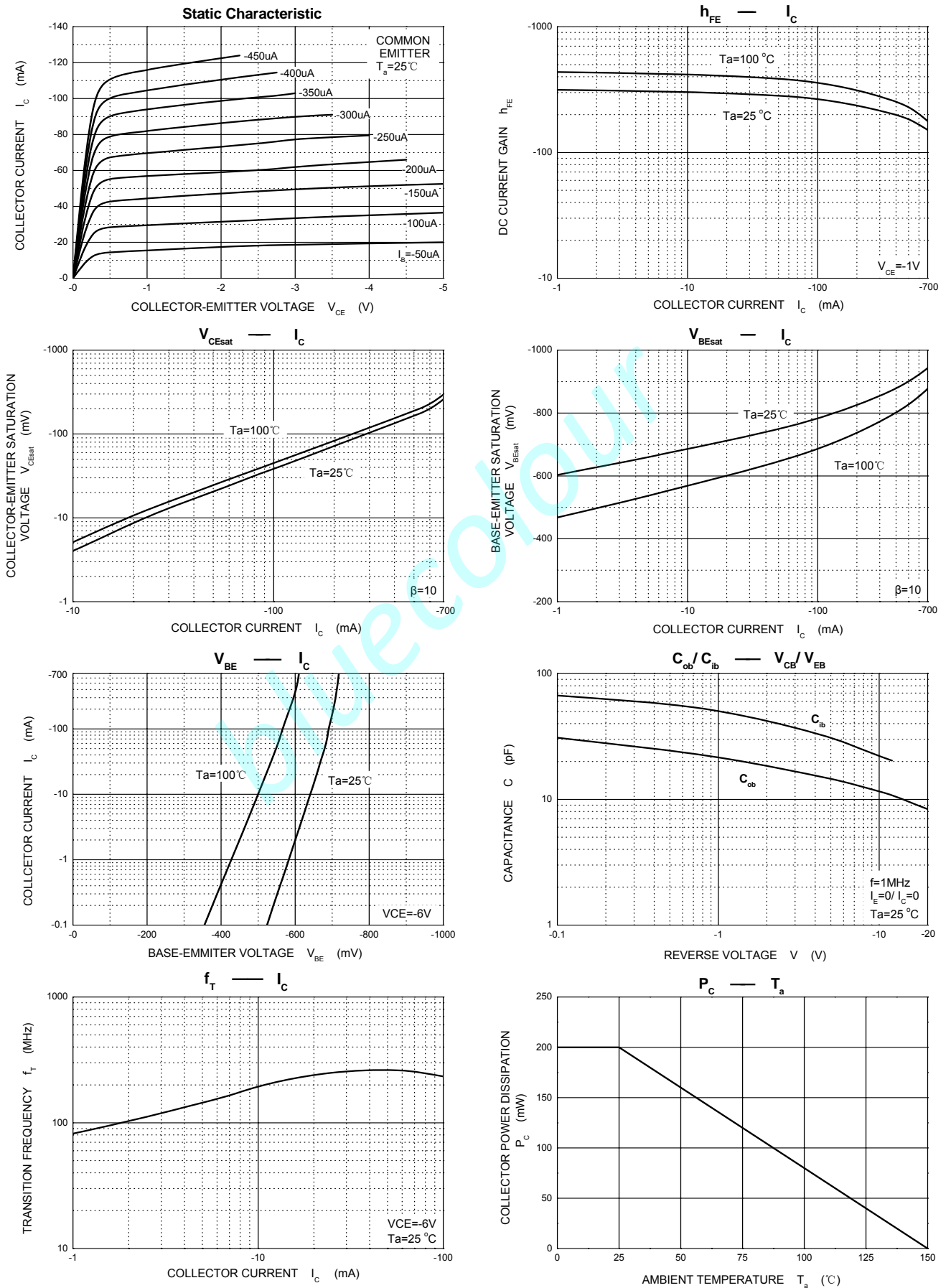
Parameter	Symbol	est conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C= -1\text{mA}, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E= -100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30\text{ V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}= -5\text{V}, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}^*$	$c_{E}=-1\text{V}, I_C= -100\text{mA}$	110		400	
	$h_{FE(2)}^*$	$c_{E}=-1\text{V}, I_C= -700\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$c_{E}=-700\text{ mA}, I_B= -70\text{mA}$			-0.6	V
Base-emitter voltage	V_{BE}^*	$c_{E}=-6\text{V}, I_C= -10\text{mA}$	-0.6		-0.7	V
Transition frequency	f_T	$V_{CE}= -6\text{V}, I_C= -10\text{mA}$		160		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-6\text{V}, I_E=0, f=1\text{MHz}$		17		pF

* Pulse test : Pulse width $\leq 350\mu\text{s}$, Duty Cycle $\leq 2\%$.

CLASSIFICATION OF $h_{FE(1)}$

Range	A	B	C	D	E
Range	110-180	135-220	170-270	200-320	250-400
Marking	BV1	BV2	BV3	BV4	BV5

Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

